# Panasonic

MOS FET FC4B21300L1

## FC4B21300L1 Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

#### Features

- Source-source ON resistance:Rss(on) typ. = 80 m $\Omega$ (VGS = 3.8 V)
- CSP(Chip Size Package)
- · RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 29

#### Packaging

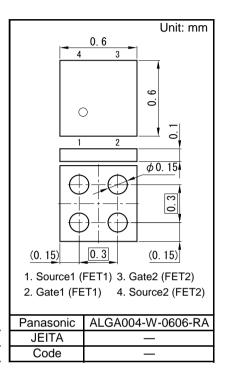
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

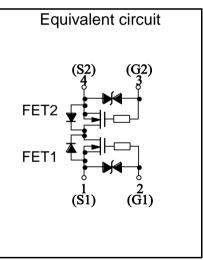
■ Absolute Maximum Ratings Ta = 25	°C			
Parameter	Symbol	Rating	Unit	
Source-source Voltage	VSS	12	V	
Gate-source Voltage	VGS	±8	V	
Source Current (DC)	IS *1	1.5	А	
	IS *2	2	Α	
Source Current (Pulsed)	ISp *3	15	А	
Total Power Dissipation	PD <sup>*1</sup>	0.32	W	
	PD *2	0.6	W	
Channel Temperature	Tch	150	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	
Thermal Resistance (ch-a)	Rth *1	390	°C/W	
	Rth *2	208	°C/W	

Note \*1 Mounted on FR4 board ( $25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$ ) using the minimum recommended pad size ( $36\mu \text{m}$  Copper).

\*2 Mounted on Ceramic substrate (70 mm × 70 mm × t1.0 mm).

\*3 t = 10  $\mu$ s, Duty Cycle  $\leq$  1 %







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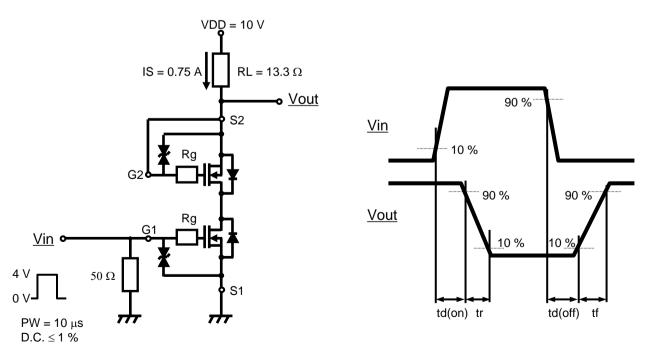
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V	
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 V, VSS = 0 V$			±10		
	1000	$VGS = \pm 5 V, VSS = 0 V$			±1.0	μA	
Gate-source Threshold Voltage	Vth	IS = 0.03 mA, VSS = 10 V	0.35	0.90	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 0.75 A, VGS = 4.5 V	55	70	95	mΩ	
	RSS(on)2	IS = 0.75 A, VGS = 3.8 V	60	80	110		
	RSS(on)3	IS = 0.75 A, VGS = 3.1 V	65	90	150		
	RSS(on)4	IS = 0.75 A, VGS = 2.5 V	70	115	225		
Body Diode Forward Voltage	VF(s-s)	IF = 0.75 A, VGS = 0 V		0.6	1.2	V	
Input Capacitance <sup>*1</sup>	Ciss			115			
Output Capacitance <sup>*1</sup>	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		25		pF	
Reverse Transfer Capacitance <sup>*1</sup>	Crss			18			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.10		116	
Rise Time <sup>*1,*2</sup>	tr	IS = 0.75 A		0.20		μS	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		0.27		μS	
Fall Time <sup>*1,*2</sup>	tf	IS = 0.75 A		0.22			
Total Gate Charge <sup>*1</sup>	Qg	VDD = 10 V		1.7			
Gate-source Charge <sup>*1</sup>	Qgs	VGS = 0 to 4.0 V,		0.5		nC	
Gate-drain Charge <sup>*1</sup>	Qgd	IS = 0.75 A		0.45			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

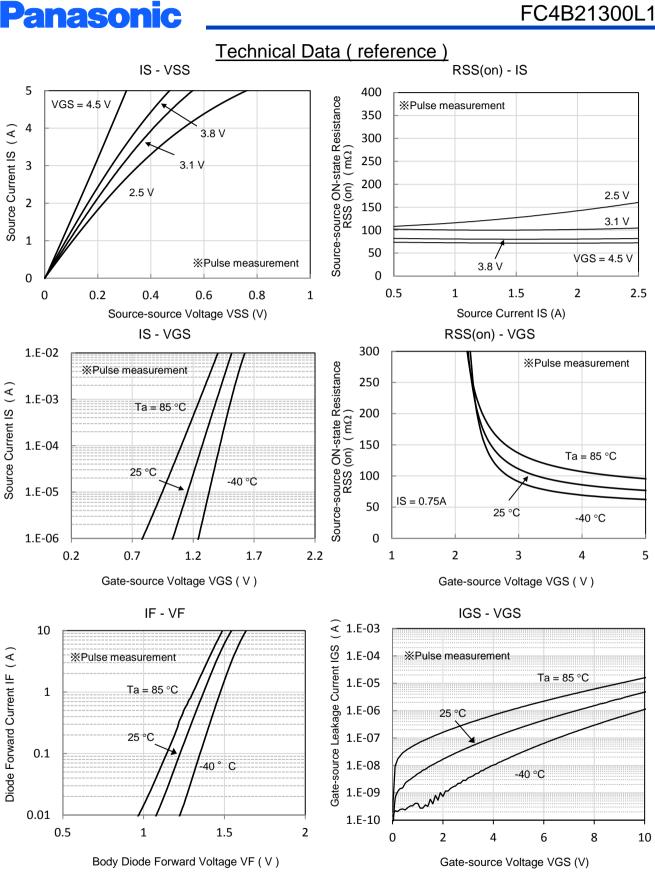
\*1 Guaranteed by design, not subject to production testing

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



Note2 : Measurement circuit

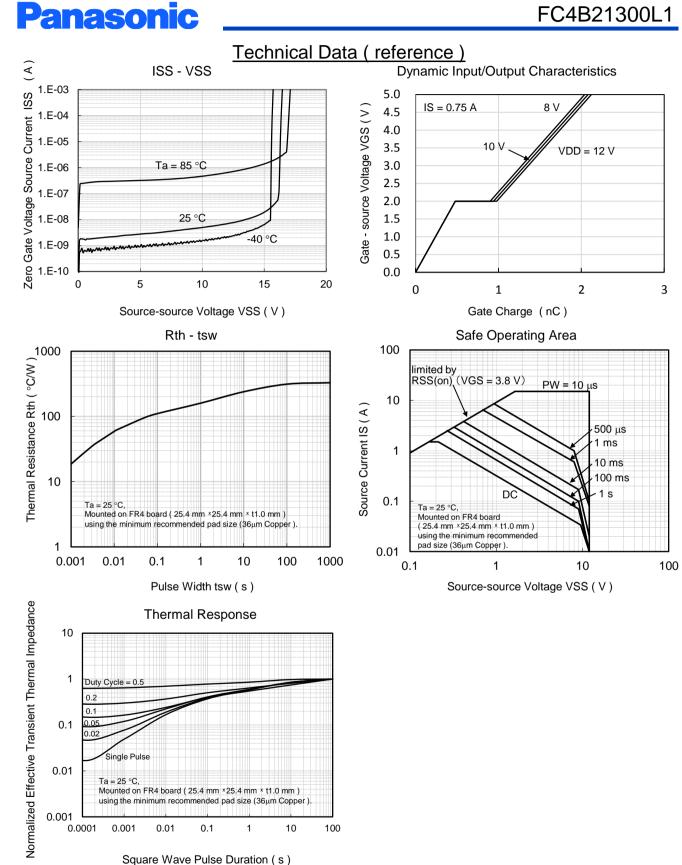
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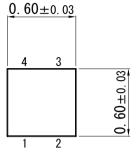
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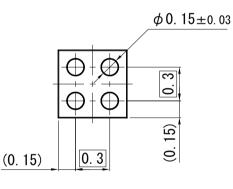
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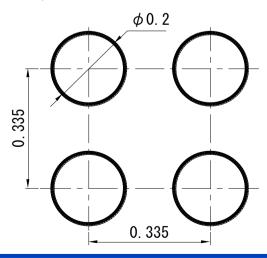
Unit: mm







■ Land Pattern (Reference)



Unit: mm

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